

Zhong-Ming Wei

List of Publications by Year in descending order

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181
papers

9,467
citations

29994

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46693

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188
all docs

188
docs citations

188
times ranked

10178
citing authors

#	ARTICLE	IF	CITATIONS
1	<scp>Polarization-sensitive</scp> and <scp>wide-spectrum</scp> photovoltaic detector based on <scp>quasi-1D ZrGeTe₄</scp> <scp>nanoribbon</scp>. InformaAnMateriily, 2022, 4, .	8.5	17
2	Intrinsic Linear Dichroism of Organic Single Crystals toward High-performance Polarization-sensitive Photodetectors. Advanced Materials, 2022, 34, e2105665.	11.1	23
3	Polarimetric Image Sensor and Fermi Level Shifting Induced Multichannel Transition Based on 2D PdPS. Advanced Materials, 2022, 34, e2107206.	11.1	29
4	Twist-angle two-dimensional superlattices and their application in (opto)electronics. Journal of Semiconductors, 2022, 43, 011001.	2.0	10
5	Electric-Field-Induced Room-Temperature Antiferroelectric-Ferroelectric Phase Transition in van der Waals Layered GeSe. ACS Nano, 2022, 16, 1308-1317.	7.3	30
6	Polarization Sensitive Solar-blind Ultraviolet Photodetectors Based on Ultrawide Bandgap KNb₃O₈ Nanobelt with Fringe-like Atomic Lattice. Advanced Functional Materials, 2022, 32, .	7.8	41
7	Polarimetric Image Sensor and Fermi Level Shifting Induced Multichannel Transition Based on 2D PdPS (Adv. Mater. 2/2022). Advanced Materials, 2022, 34, .	11.1	1
8	Recombination Time Mismatch and Spin Dependent Photocurrent at a Ferromagnetic-Metal-Semiconductor Tunnel Junction. Physical Review Letters, 2022, 128, 057701.	2.9	4
9	ä»æ—â±,çšŕä½žç»‘ăšă~¼ă½“çš,,âæCE-â...%æžæµ<â™™“. Chinese Science Bulletin, 2022, , .	0.4	1
10	Band-like Charge Transport in Small-molecule Thin Film toward High-performance Organic Phototransistors at Low Temperature. Advanced Optical Materials, 2022, 10, .	3.6	4
11	Wide-spectrum polarization-sensitive and fast-response photodetector based on 2D group IV-VI semiconductor tin selenide. Fundamental Research, 2022, 2, 985-992.	1.6	8
12	2D Ultrawide Bandgap Semiconductors: Odyssey and Challenges. Small Methods, 2022, 6, e2101348.	4.6	18
13	Band offset trends in IV-VI layered semiconductor heterojunctions. Journal of Physics Condensed Matter, 2022, 34, 195003.	0.7	3
14	Recent progress in optoelectronic applications of hybrid 2D/3D silicon-based heterostructures. Science China Materials, 2022, 65, 876-895.	3.5	9
15	Room-temperature Near-infrared Excitonic Lasing from Mechanically Exfoliated InSe Microflake. ACS Nano, 2022, 16, 1477-1485.	7.3	11
16	Near-Infrared Polarimetric Image Sensors Based on Ordered Sulfur-Passivation GaSb Nanowire Arrays. ACS Nano, 2022, 16, 8128-8140.	7.3	22
17	Engineering Near-Infrared Light Emission in Mechanically Exfoliated InSe Platelets through Hydrostatic Pressure for Multicolor Microlasing. Nano Letters, 2022, 22, 3840-3847.	4.5	11
18	Cation-Alloying-Induced Blue-shifted and Wide-spectrum Polarization-sensitive Photodetection in Quasi-1D SbBiS₃. Small Structures, 2022, 3, .	6.9	10

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19	Optical and electronic anisotropy of a 2D semiconductor SiP. Nano Research, 2022, 15, 8579-8586.	5.8	8
20	Polarization Sensitive Solar-Blind Ultraviolet Photodetectors Based on Ultrawide Bandgap KNb ₃ O ₈ Nanobelt with Fringe-Like Atomic Lattice (Adv. Funct. Mater. 24/2022). Advanced Functional Materials, 2022, 32, .	7.8	1
21	Cation-Alloying-Induced Blue-Shifted and Wide-Spectrum Polarization-Sensitive Photodetection in Quasi-1D SbBiS ₃ . Small Structures, 2022, 3, .	6.9	0
22	Application of transition metal dichalcogenides in mid-infrared fiber laser. Nano Select, 2021, 2, 37-46.	1.9	13
23	Extrinsic Photoconduction Induced Short-Wavelength Infrared Photodetectors Based on Ge-Based Chalcogenides. Small, 2021, 17, e2006765.	5.2	25
24	In-Plane Optical and Electrical Anisotropy of 2D Black Arsenic. ACS Nano, 2021, 15, 1701-1709.	7.3	41
25	Direct Polarimetric Image Sensor and Wide Spectral Response Based on Quasi-1D Sb ₂ S ₃ Nanowire. Advanced Functional Materials, 2021, 31, 2006601.	7.8	52
26	Effectively modulating thermal activated charge transport in organic semiconductors by precise potential barrier engineering. Nature Communications, 2021, 12, 21.	5.8	51
27	Direct Synthesis and Enhanced Rectification of Alloy-to-Alloy 2D Type-II MoS ₂ (1-x)/Se ₂ (x)/SnS ₂ (1-x) Heterostructures. Advanced Materials, 2021, 33, e2006908.		
28	Vertical Heterostructures: Direct Synthesis and Enhanced Rectification of Alloy-to-Alloy 2D Type-II MoS ₂ (1-x)/Se ₂ (x)/SnS ₂ (1-x) Heterostructures (Adv. Mater. 8/2021). Advanced Materials, 2021, 33, 2170059.		
29	Flexible Sensors Based on Organic-Inorganic Hybrid Materials. Advanced Materials Technologies, 2021, 6, 2000889.	3.0	43
30	Quantum Confinement Effects on Excitonic Properties in the 2D vdW quantum system: The ZnO/WSe ₂ Case. Advanced Photonics Research, 2021, 2, 2000114.	1.7	5
31	Nondegenerate P-Type In-Doped SnS ₂ Monolayer Transistor. Advanced Electronic Materials, 2021, 7, 2001168.	2.6	13
32	Van der Waals epitaxial growth of air-stable CrSe ₂ nanosheets with thickness-tunable magnetic order. Nature Materials, 2021, 20, 818-825.	13.3	206
33	Anomalous Hall effect in graphene coupled to a layered magnetic semiconductor. Physical Review B, 2021, 103, .	1.1	8
34	Cross-Substitution Promoted Ultrawide Bandgap up to 4.5 eV in a 2D Semiconductor: Gallium Thiophosphate. Advanced Materials, 2021, 33, e2008761.	11.1	41
35	The More, the Better—Recent Advances in Construction of 2D Multi-Heterostructures. Advanced Functional Materials, 2021, 31, 2102049.	7.8	27
36	Birefringence and Dichroism in Quasi-1D Transition Metal Trichalcogenides: Direct Experimental Investigation. Small, 2021, 17, e2100457.	5.2	17

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37	Short-Wave Near-Infrared Polarization Sensitive Photodetector Based on GaSb Nanowire. IEEE Electron Device Letters, 2021, 42, 549-552.	2.2	31
38	Low-Noise Dual-Band Polarimetric Image Sensor Based on 1D Bi ₂ S ₃ Nanowire. Advanced Science, 2021, 8, e2100075.	5.6	48
39	Transition Metal Trichalcogenides: Birefringence and Dichroism in Quasi-1D Transition Metal Trichalcogenides: Direct Experimental Investigation (Small 21/2021). Small, 2021, 17, 2170098.	5.2	0
40	Ferroelectric-tuned van der Waals heterojunction with band alignment evolution. Nature Communications, 2021, 12, 4030.	5.8	79
41	Photodetectors: Cross-Substitution Promoted Ultrawide Bandgap up to 4.5 eV in a 2D Semiconductor: Gallium Thiophosphate (Adv. Mater. 22/2021). Advanced Materials, 2021, 33, 2170169.	11.1	0
42	Large Perpendicular Magnetic Anisotropy in Ta/CoFeB/MgO on Full-Coverage Monolayer MoS ₂ and First-Principles Study of Its Electronic Structure. ACS Applied Materials & Interfaces, 2021, 13, 32579-32589.	4.0	11
43	Intermediate anomalous Hall states induced by noncollinear spin structure in the magnetic topological insulator $MnBi_7$. Physical Review B, 2021, 104, .	11.7	7
44	Decoupling of the Electrical and Thermal Transports in Strongly Coupled Interlayer Materials. Journal of Physical Chemistry Letters, 2021, 12, 7832-7839.	2.1	8
45	Tunable Alloying Improved Wide Spectrum UV-Vis-NIR and Polarization-Sensitive Photodetector Based on Sb ² Se Nanowires. IEEE Transactions on Electron Devices, 2021, 68, 3887-3893.	1.6	15
46	Strain driven band alignment transition of the ferromagnetic VS ₂ /C ₃ N van der Waals heterostructure*. Chinese Physics B, 2021, 30, 097507.	0.7	3
47	Gate-controlled ambipolar transport in b-AsP crystals and their VIS-NIF photodetection. Nanoscale, 2021, 13, 10579-10586.	2.8	15
48	When graphene meets white graphene – recent advances in the construction of graphene and h-BN heterostructures. Nanoscale, 2021, 13, 13174-13194.	2.8	9
49	Reversible Half Wave Rectifier Based on 2D InSe/GeSe Heterostructure with Near-Broken Band Alignment. Advanced Science, 2021, 8, 1903252.	5.6	38
50	Polarizer-free polarimetric image sensor through anisotropic two-dimensional GeSe. Science China Materials, 2021, 64, 1230-1237.	3.5	21
51	Excitons in two-dimensional van der Waals heterostructures. Journal Physics D: Applied Physics, 2021, 54, 053001.	1.3	8
52	Integrated polarization-sensitive amplification system for digital information transmission. Nature Communications, 2021, 12, 6476.	5.8	53
53	Strain-engineering on GeSe: Raman spectroscopy study. Physical Chemistry Chemical Physics, 2021, 23, 26997-27004.	1.3	2
54	Continuous orientated growth of scaled single-crystal 2D monolayer films. Nanoscale Advances, 2021, 3, 6545-6567.	2.2	3

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55	Polarized photodetectors based on two-dimensional semiconductors. Science China: Physics, Mechanics and Astronomy, 2020, 63, 1.	2.0	4
56	Temperature dependence of charge transport in solid-state molecular junctions based on oligo(phenylene ethynylene)s. Nanotechnology, 2020, 31, 164001.	1.3	2
57	Recent advances in low-dimensional semiconductor nanomaterials and their applications in high-performance photodetectors. Informa π -Materi π ly, 2020, 2, 291-317.	8.5	103
58	Iron-doping induced multiferroic in two-dimensional In ₂ Se ₃ . Science China Materials, 2020, 63, 421-428.	3.5	30
59	Relieving the Photosensitivity of Organic Field-Effect Transistors. Advanced Materials, 2020, 32, e1906122.	11.1	61
60	Quasiparticle Band Structure and Optical Properties of the Janus Monolayer and Bilayer SnSSe. Journal of Physical Chemistry C, 2020, 124, 23832-23838.	1.5	23
61	Intercalation of Two-dimensional Layered Materials. Chemical Research in Chinese Universities, 2020, 36, 584-596.	1.3	21
62	Spin-Valve Effect in Fe ₃ GeTe ₂ /MoS ₂ /Fe ₃ GeTe ₂ van der Waals Heterostructures. ACS Applied Materials & Interfaces, 2020, 12, 43921-43926.	4.0	109
63	Visible Phototransistors Based on Vertical Nanolayered Heterostructures of SnS/SnS ₂ and SnSe ₂ /SnS ₂ nanoflakes. ACS Applied Nano Materials, 2020, 3, 6847-6854.	2.4	19
64	Orbital localization induced magnetization in nonmetal-doped phosphorene. Journal Physics D: Applied Physics, 2020, 53, 155001.	1.3	4
65	From negative to positive magnetoresistance in the intrinsic magnetic topological insulator MnB ₂ T. $T \ll T_c$	1.1	23
66	Recent Advances of 2D Materials in Nonlinear Photonics and Fiber Lasers. Advanced Optical Materials, 2020, 8, 1901631.	3.6	122
67	Saturable absorption properties and femtosecond mode-locking application of titanium trisulfide. Applied Physics Letters, 2020, 116, .	1.5	49
68	Polarization-Sensitive Photodetectors: Symmetry-Reduction Enhanced Polarization-Sensitive Photodetection in Core-Shell Sb ₃ S ₂ O ₃ van der Waals Heterostructure (Small 7/2020). Small, 2020, 16, 2070036.	5.2	1
69	Symmetry-Reduction Enhanced Polarization-Sensitive Photodetection in Core-Shell Sb ₃ S ₂ O ₃ van der Waals Heterostructure. Small, 2020, 16, e1907172.	5.2	32
70	Preparing two-dimensional crystalline conjugated polymer films by synergetic polymerization and self-assembly at air/water interface. Polymer Chemistry, 2020, 11, 1572-1579.	1.9	9
71	Non-layered ZnSb nanoplates for room temperature infrared polarized photodetectors. Journal of Materials Chemistry C, 2020, 8, 6388-6395.	2.7	24
72	Strong Anisotropy and Piezoelectric Phototronic Effect in SnO ₂ Microwires. Advanced Electronic Materials, 2020, 6, 1901441.	2.6	15

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73	Mixed Valence Driven Quasi 1D Sn ^{II} /Sn ^{IV} S ₃ with Highly Polarization Sensitive UV-vis-NIR Photoresponse. <i>Advanced Functional Materials</i> , 2019, 29, 1904416.	7.8	39
74	Direct Wide Bandgap 2D GeSe ₂ Monolayer toward Anisotropic UV Photodetection. <i>Advanced Optical Materials</i> , 2019, 7, 1900622.	3.6	70
75	Electronic structures, magnetic properties and lattice strain effects of quaternary Heusler alloys RuMnCrZ (Z = Ni, Co, P, As, Sb). <i>Journal Physics D: Applied Physics</i> , 2019, 52, 505003.	1.3	3
76	Machine learning in materials science. <i>Informa Mater</i> , 2019, 1, 338-358.	8.5	427
77	Nonvolatile memristor based on heterostructure of 2D room-temperature ferroelectric In ₂ Se ₃ and WSe ₂ . <i>Science China Information Sciences</i> , 2019, 62, 1.	2.7	29
78	Two-dimensional XSe ₂ (X = Mn, V) based magnetic tunneling junctions with high Curie temperature*. <i>Chinese Physics B</i> , 2019, 28, 107504.	0.7	22
79	Perseverance of direct bandgap in multilayer 2D PbI ₂ under an experimental strain up to 7.69%. <i>2D Materials</i> , 2019, 6, 025014.	2.0	20
80	A ternary SnS _{1.26} Se _{0.76} alloy for flexible broadband photodetectors. <i>RSC Advances</i> , 2019, 9, 14352-14359.	1.7	7
81	Optical and electrical properties of two-dimensional anisotropic materials. <i>Journal of Semiconductors</i> , 2019, 40, 061001.	2.0	65
82	Multifunctional Photodetectors Based on Nanolayered Black Phosphorus/SnS _{0.5} Se _{1.5} Heterostructures. <i>ACS Applied Nano Materials</i> , 2019, 2, 3548-3555.	2.4	10
83	Metal Chalcogenides: Versatile Crystal Structures and (Opto)electronic Applications of the 2D Metal Mono-, Di-, and Tri-Chalcogenide Nanosheets (Adv. Funct. Mater. 24/2019). <i>Advanced Functional Materials</i> , 2019, 29, 1970161.	7.8	2
84	Highly Polarized Photoelectrical Response in vdW ZrS ₃ Nanoribbons. <i>Advanced Electronic Materials</i> , 2019, 5, 1900419.	2.6	45
85	Influence of solid-state electrolyte on 2D SnS ₂ field effect transistors. <i>Materials Research Express</i> , 2019, 6, 086320.	0.8	3
86	Thickness-Dependent Ultrafast Photonics of SnS ₂ Nanolayers for Optimizing Fiber Lasers. <i>ACS Applied Nano Materials</i> , 2019, 2, 2697-2705.	2.4	48
87	Versatile Crystal Structures and (Opto)electronic Applications of the 2D Metal Mono-, Di-, and Tri-Chalcogenide Nanosheets. <i>Advanced Functional Materials</i> , 2019, 29, 1900040.	7.8	58
88	2D Functional Systems: Recent Advances in the Functional 2D Photonic and Optoelectronic Devices (Advanced Optical Materials 3/2019). <i>Advanced Optical Materials</i> , 2019, 7, 1970010.	3.6	0
89	Magnetic and transport properties of a ferromagnetic layered semiconductor MnIn ₂ Se ₄ . <i>Applied Physics Letters</i> , 2019, 115, .	1.5	8
90	p-MoS ₂ /n-InSe van der Waals heterojunctions and their applications in all-2D optoelectronic devices. <i>RSC Advances</i> , 2019, 9, 35039-35044.	1.7	15

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91	Band-like transport in small-molecule thin films toward high mobility and ultrahigh detectivity phototransistor arrays. <i>Nature Communications</i> , 2019, 10, 12.	5.8	172
92	The Coulomb interaction in van der Waals heterostructures. <i>Science China: Physics, Mechanics and Astronomy</i> , 2019, 62, 1.	2.0	25
93	Tunable Schottky barrier width and enormously enhanced photoresponsivity in Sb doped SnS ₂ monolayer. <i>Nano Research</i> , 2019, 12, 463-468.	5.8	71
94	Press-engineered funnel effect in MoS ₂ monolayer homojunction. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 055103.	1.3	1
95	Electronic structure and exciton shifts in Sb-doped MoS ₂ monolayer. <i>Npj 2D Materials and Applications</i> , 2019, 3, .	3.9	82
96	Growth of two-dimensional materials on hexagonal boron nitride (h-BN). <i>Nanotechnology</i> , 2019, 30, 034003.	1.3	19
97	Recent Advances in the Functional 2D Photonic and Optoelectronic Devices. <i>Advanced Optical Materials</i> , 2019, 7, 1801274.	3.6	209
98	Multistate Logic Inverter Based on Black Phosphorus/SnSeS Heterostructure. <i>Advanced Electronic Materials</i> , 2019, 5, 1800416.	2.6	24
99	Graphyne and Its Family: Recent Theoretical Advances. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 2692-2706.	4.0	156
100	Recent progress in polarization-sensitive photodetectors based on low-dimensional semiconductors. <i>Wuli Xuebao/Acta Physica Sinica</i> , 2019, 68, 163201.	0.2	11
101	Highly polarization sensitive photodetectors based on quasi-1D titanium trisulfide (TiS ₃). <i>Nanotechnology</i> , 2018, 29, 184002.	1.3	67
102	Type-II Transition Metal Dichalcogenides Lateral Homojunctions: Layer Thickness and External Electric Field Effects. <i>Small</i> , 2018, 14, e1800365.	5.2	41
103	Tunable electric properties of bilayer InSe with different interlayer distances and external electric field. <i>Semiconductor Science and Technology</i> , 2018, 33, 034002.	1.0	9
104	Toward High-Performance Photodetectors Based on 2D Materials: Strategy on Methods. <i>Small Methods</i> , 2018, 2, 1700349.	4.6	118
105	Two-dimensional n-p-InSe/GeSe(SnS) van der Waals heterojunctions: High carrier mobility and broadband performance. <i>Physical Review B</i> , 2018, 97, ..	1.1	113
106	Diamine anchored molecular junctions of oligo(phenylene ethynylene) cruciform. <i>Chinese Chemical Letters</i> , 2018, 29, 271-275.	4.8	8
107	Chemical vapor deposition growth of two-dimensional heterojunctions. <i>Science China: Physics, Mechanics and Astronomy</i> , 2018, 61, 1.	2.0	52
108	Perpendicular Optical Reversal of the Linear Dichroism and Polarized Photodetection in 2D GeAs. <i>ACS Nano</i> , 2018, 12, 12416-12423.	7.3	157

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109	Large tunneling magnetoresistance in magnetic tunneling junctions based on two-dimensional CrX ₃ (X = Br, I) monolayers. <i>Nanoscale</i> , 2018, 10, 22196-22202.	2.8	44
110	Field-Effect Transistors: Thickness-Dependent Carrier Transport Characteristics of a New 2D Elemental Semiconductor: Black Arsenic (Adv. Funct. Mater. 43/2018). <i>Advanced Functional Materials</i> , 2018, 28, 1870312.	7.8	2
111	Thickness-Dependent Carrier Transport Characteristics of a New 2D Elemental Semiconductor: Black Arsenic. <i>Advanced Functional Materials</i> , 2018, 28, 1802581.	7.8	125
112	Tunable electronic and optical properties of InSe/InTe van der Waals heterostructures toward optoelectronic applications. <i>Journal of Materials Chemistry C</i> , 2018, 6, 7201-7206.	2.7	87
113	Various Structures of 2D Transition-Metal Dichalcogenides and Their Applications. <i>Small Methods</i> , 2018, 2, 1800094.	4.6	107
114	Type-II InSe/MoSe ₂ (WSe ₂) van der Waals heterostructures: vertical strain and electric field effects. <i>Journal of Materials Chemistry C</i> , 2018, 6, 10010-10019.	2.7	59
115	Highly anisotropic solar-blind UV photodetector based on large-size two-dimensional $\sqrt{3}\times\sqrt{3}$ -MoO ₃ atomic crystals. <i>2D Materials</i> , 2018, 5, 035033.	2.0	49
116	Black Arsenic: A Layered Semiconductor with Extreme In-Plane Anisotropy. <i>Advanced Materials</i> , 2018, 30, e1800754.	11.1	161
117	Turning a disadvantage into an advantage: synthesizing high-quality organometallic halide perovskite nanosheet arrays for humidity sensors. <i>Journal of Materials Chemistry C</i> , 2017, 5, 2504-2508.	2.7	74
118	Tunable Schottky Barrier at MoSe ₂ /Metal Interfaces with a Buffer Layer. <i>Journal of Physical Chemistry C</i> , 2017, 121, 9305-9311.	1.5	45
119	A type-II GeSe/SnS heterobilayer with a suitable direct gap, superior optical absorption and broad spectrum for photovoltaic applications. <i>Journal of Materials Chemistry A</i> , 2017, 5, 13400-13410.	5.2	138
120	Light induced double σ state anti-ambipolar behavior and self-driven photoswitching in p-WSe ₂ /n-SnS ₂ heterostructures. <i>2D Materials</i> , 2017, 4, 025097.	2.0	59
121	High-performance photodetectors based on Sb ₂ S ₃ nanowires: wavelength dependence and wide temperature range utilization. <i>Nanoscale</i> , 2017, 9, 12364-12371.	2.8	72
122	Electric field induced electronic properties modification of ZrS ₂ /HfS ₂ van der Waals heterostructure. <i>RSC Advances</i> , 2017, 7, 14625-14630.	1.7	28
123	Large-scale 2D PbI ₂ monolayers: experimental realization and their indirect band-gap related properties. <i>Nanoscale</i> , 2017, 9, 3736-3741.	2.8	98
124	Short-Wave Near-Infrared Linear Dichroism of Two-Dimensional Germanium Selenide. <i>Journal of the American Chemical Society</i> , 2017, 139, 14976-14982.	6.6	286
125	A two-dimensional Fe-doped SnS ₂ magnetic semiconductor. <i>Nature Communications</i> , 2017, 8, 1958.	5.8	315
126	Type-I Ca(OH) ₂ /MoTe ₂ vdW heterostructure for ultraviolet optoelectronic device applications: electric field effects. <i>Journal of Materials Chemistry C</i> , 2017, 5, 12629-12634.	2.7	25

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127	Role of defects in enhanced Fermi level pinning at interfaces between metals and transition metal dichalcogenides. <i>Physical Review B</i> , 2017, 96, .	1.1	26
128	Tunable Electronic Structures of GeSe Nanosheets and Nanoribbons. <i>Journal of Physical Chemistry C</i> , 2017, 121, 14373-14379.	1.5	62
129	Electric field-tunable electronic structures of 2D alkaline-earth metal hydroxide-graphene heterostructures. <i>Journal of Materials Chemistry C</i> , 2017, 5, 7230-7235.	2.7	21
130	Electrostatic gating dependent multiple-band alignments in a high-temperature ferromagnetic Mg(OH) heterobilayer. <i>Physical Review B</i> , 2017, 95, .	1.1	39
131	Composition-tunable 2D SnSe ₂ (1-x)S _{2x} alloys towards efficient bandgap engineering and high performance (opto)electronics. <i>Journal of Materials Chemistry C</i> , 2017, 5, 84-90.	2.7	81
132	Tuned polarity and enhanced optoelectronic performances of few-layer Nb _{0.125} Re _{0.875} Se ₂ flakes. <i>Applied Physics Letters</i> , 2016, 109, 112102.	1.5	7
133	Flexible photodetectors based on phase dependent PbI ₂ single crystals. <i>Journal of Materials Chemistry C</i> , 2016, 4, 6492-6499.	2.7	93
134	Direct Vapor Phase Growth and Optoelectronic Application of Large Band Offset SnS ₂ /MoS ₂ Vertical Bilayer Heterostructures with High Lattice Mismatch. <i>Advanced Electronic Materials</i> , 2016, 2, 1600298.	2.6	155
135	An Efficient and Low-Cost Photolithographic Pattern Transfer Technique to Fabricate Electrode Arrays for Micro/Nanoelectronics. <i>Advanced Materials Technologies</i> , 2016, 1, 1600001.	3.0	27
136	Co-nucleus 1D/2D Heterostructures with Bi ₂ S ₃ Nanowire and MoS ₂ Monolayer: One-Step Growth and Defect-Induced Formation Mechanism. <i>ACS Nano</i> , 2016, 10, 8938-8946.	7.3	82
137	Gate-tunable diode-like current rectification and ambipolar transport in multilayer van der Waals ReSe ₂ /WS ₂ p-n heterojunctions. <i>Physical Chemistry Chemical Physics</i> , 2016, 18, 27750-27753.	1.3	30
138	Large-Size 2D Cu ₂ S Nanosheets with Giant Phase Transition Temperature Lowering (120 K) Synthesized by a Novel Method of Super-Cooling Chemical Vapor Deposition. <i>Advanced Materials</i> , 2016, 28, 8271-8276.	11.1	57
139	Anti-Ambipolar Field-Effect Transistors Based On Few-Layer 2D Transition Metal Dichalcogenides. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 15574-15581.	4.0	77
140	Enhanced rectification, transport property and photocurrent generation of multilayer ReSe ₂ /MoS ₂ p-n heterojunctions. <i>Nano Research</i> , 2016, 9, 507-516.	5.8	132
141	Wavelength dependent UV-Vis photodetectors from SnS ₂ flakes. <i>RSC Advances</i> , 2016, 6, 422-427.	1.7	57
142	Strain induced piezoelectric effect in black phosphorus and MoS ₂ van der Waals heterostructure. <i>Scientific Reports</i> , 2015, 5, 16448.	1.6	88
143	Tunable Polarity Behavior and Self-Driven Photoswitching in WSe ₂ /WS ₂ Heterojunctions. <i>Small</i> , 2015, 11, 5430-5438.	5.2	114
144	Gate-Tunable Ultrahigh Photoresponsivity of 2D Heterostructures Based on Few Layer MoS ₂ and Solution-Processed rGO. <i>Advanced Electronic Materials</i> , 2015, 1, 1500267.	2.6	28

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145	Improving the Field-Effect Performance of Bi ₂ S ₃ Single Nanowires by an Asymmetric Device Fabrication. <i>ChemPhysChem</i> , 2015, 16, 99-103.	1.0	18
146	Molecular Heterojunctions of Oligo(phenylene ethynylene)s with Linear to Cruciform Framework. <i>Advanced Functional Materials</i> , 2015, 25, 1700-1708.	7.8	29
147	Gas-dependent photoresponse of SnS nanoparticles-based photodetectors. <i>Journal of Materials Chemistry C</i> , 2015, 3, 1397-1402.	2.7	86
148	Synthesis and Transport Properties of Large-Scale Alloy Co _{0.16} Mo _{0.84} S ₂ Bilayer Nanosheets. <i>ACS Nano</i> , 2015, 9, 1257-1262.	7.3	79
149	Electric-Field Tunable Band Offsets in Black Phosphorus and MoS ₂ van der Waals p-n Heterostructure. <i>Journal of Physical Chemistry Letters</i> , 2015, 6, 2483-2488.	2.1	193
150	Novel Optical and Electrical Transport Properties in Atomically Thin WSe ₂ /MoS ₂ p-n Heterostructures. <i>Advanced Electronic Materials</i> , 2015, 1, 1400066.	2.6	67
151	Role of redox centre in charge transport investigated by novel self-assembled conjugated polymer molecular junctions. <i>Nature Communications</i> , 2015, 6, 7478.	5.8	43
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